



SiHK031N60AE / SiHK039N60AEF / SiHK075N60AEF

Gen 5 600 V Superjunction MOSFETs in PowerPAK® 10 x 12

LATEST GEN 5 600 V SUPERJUNCTION TECHNOLOGY

- Industry-low $R_{DS(on)}$
- Boosts system efficiency
- Enables higher power ratings and power density
- High I_D current capability

GREAT THERMAL CAPABILITY OF POWERPAK® 10 x 12 FUSE LEAD PACKAGE

- Low profile, dimensions: 9.9 mm x 11.7 mm x 2.3 mm
- T0 leadless package
- Integrated Kelvin source connection
- Enables increased current density

Part Numbers	V_{DS}	$R_{DS(on)_{Typ}}$ (mΩ)	Q_g (nC)	Q_{gd} (nC)
SiHK031N60AE	600	36.8	97	32
SiHK039N60AEF	600	39	102	35
SiHK075N60AEF	600	65	62	21



For 3 kW – 10 kW
Power Supply
Solutions



APPLICATIONS



AI SERVERS



SOLAR
INVERTERS



SERVERS / DATA
CENTERS



GAMING
PCs



TELECOM



UPS

www.vishay.com

TARGET CIRCUITS

The E Series SiHK031N60AE fits low frequency applications, while the EF Series SiHK039N60AEF / SiHK075N60AEF fits soft switching topologies

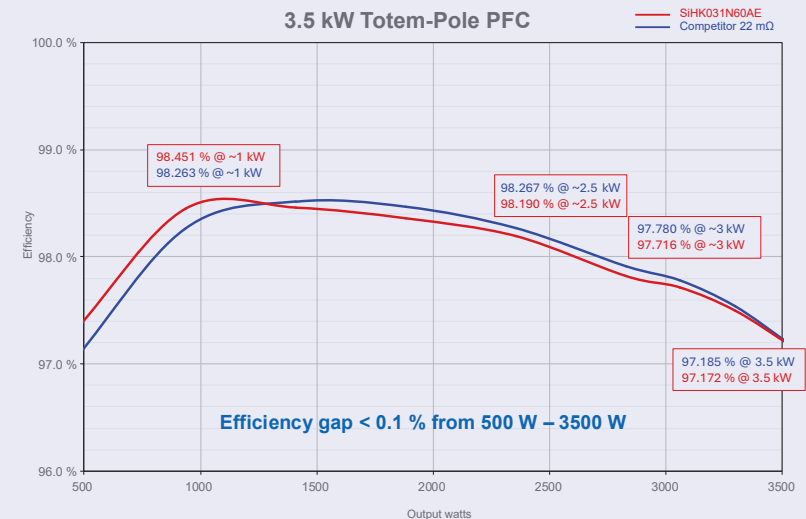
SiHK031N60AE

- Slow switch for totem-pole PFC
- Line rectifier, e.g. active bridge PFC
- Inrush current relay circuit

SiHK039N60AEF / SiHK075N60AEF

- LLC resonant converter
- Phase shift full bridge

Our Gen 5 600 V Superjunction MOSFETs in the PowerPAK® 10 x 12 Package Enable Lower $R_{DS(on)}$ to Boost Efficiency in Power Systems



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